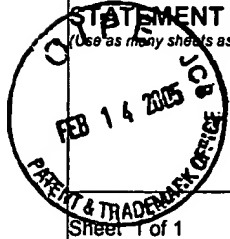


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Application Number	09/945,535
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

Attorney Docket No: 1303.026US1

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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional) <sup>2</sup> Applicant to place a check mark here if English language Translation is attached

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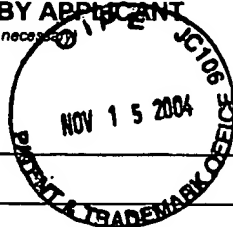
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First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

Sheet 1 of 1

Attorney Docket No: 1303.026US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>2</sup>
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Sheet 1 of 1

Attorney Docket No: 1303.026US1

**US PATENT DOCUMENTS**

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Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
DSP		KIM, D. , et al., "Atomic Control of Substrate Termination and Heteroepitaxial Growth of SrTiO <sub>3</sub> /LaAlO <sub>3</sub> Films", <u>Journal of the Korean Physical Society Vol. 36 No.6, (06/2000),444-448</u>	
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